

Silicon NPN Power Transistors

2SC3280

DESCRIPTION

- With TO-3PL package
- Complement to type 2SA1301

APPLICATIONS

- Power amplifier applications
- Recommended for 80W high fidelity audio frequency amplifier output stage

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

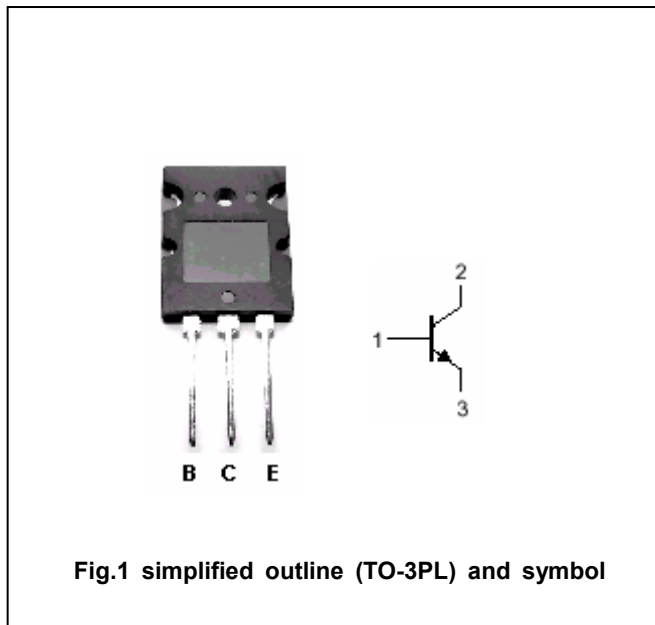


Fig.1 simplified outline (TO-3PL) and symbol

Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CB0</sub>	Collector-base voltage	Open emitter	160	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	160	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	5	V
I <sub>C</sub>	Collector current		12	A
I <sub>B</sub>	Base current		1.2	A
P <sub>C</sub>	Collector power dissipation	T <sub>C</sub> =25°C	120	W
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-55~150	°C

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## CHARACTERISTICS

T<sub>j</sub>=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =50mA ; I <sub>B</sub> =0	160			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =8A I <sub>B</sub> =0.8A			2.5	V
V <sub>BE</sub>	Base-emitter voltage	I <sub>C</sub> =6A ; V <sub>CE</sub> =5V			1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =160V I <sub>E</sub> =0			5	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			5	μA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =1A ; V <sub>CE</sub> =5V	55		160	
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =6A ; V <sub>CE</sub> =5V	35			
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =1A ; V <sub>CE</sub> =5V		30		MHz
C <sub>OB</sub>	Collector output capacitance	f=1MHz; V <sub>CB</sub> =10V		220		pF

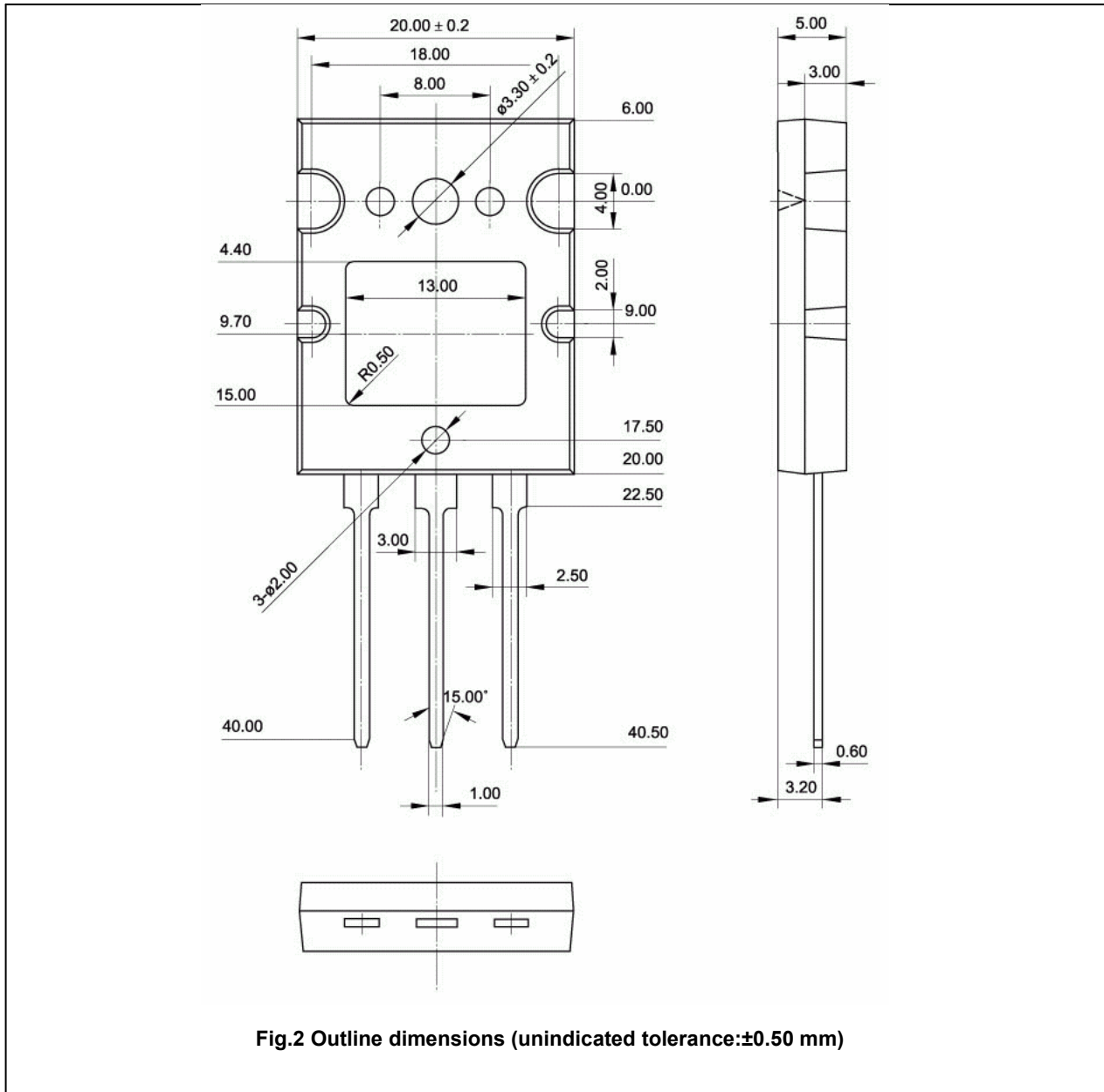
◆ h<sub>FE-1</sub> classifications

R	O
55-110	80-160

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PACKAGE OUTLINE



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